NSN 5961-00-724-5536

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View Online at https://aerobasegroup.com/nsn/5961-00-724-5536
Inclosure Material:
Metal
Overall Length:
Between 0.480 inches and 0.535 inches
Overall Diameter:
Between 0.745 inches and 0.775 inches
Mounting Facility Quantity:
1
Internal Configuration:
Junction contact
Electrode Internally-electrically Connected To Case:
Collector
Mounting Method:
Threaded stud
Features Provided:
Hermetically sealed case
Overall Width Across Flats:
Between 0.855 inches and 0.875 inches
Thread Size:
0.312 inches
Criticality Code Justification:
Feat
Semiconductor Material:
Silicon
Voltage Rating In Volts Per Characteristic:
125.0 breakdown voltage, collector-to-base, emitter open and 6.0 breakdown voltage, emitter-to-base, collector open and 80.0
breakdown voltage, collector-to-emitter, base open
Current Rating Per Characteristic:
20.00 amperes source cutoff current and 10.00 amperes source cutoff current
Power Rating Per Characteristic:
150.0 watts small-signal input power, common-collector
Maximum Operating Tempurature Per Measurement Point:
200.0 degrees celsius junction
Special Features:
Weapon system essential; junction pattern arrangement: npn
Thread Series Designator:
Unf
Terminal Type And Quantity:
2 tab, solder lug and 1 wire hook
Specification Data:

N/a

Shelf Life:

80131-release4129 professional/industrial association specification

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Demilitarization:

No

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